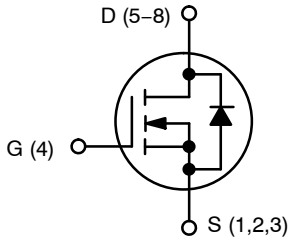
MOSFET – Power, Single N-Channel, STD Gate, SO8FL

80 V, 1.9 mΩ, 201 A

NVMFWS1D9N08X

$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D MAX
80 V	1.9 mΩ @ 10 V	201 A



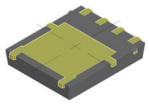
N–CHANNEL MOSFET

Features

- Low QRR, Soft Recovery Body Diode
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low QG and Capacitance to Minimize Driver Losses
- AEC Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Fre e and are RoHS Compliant

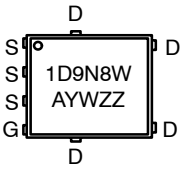
Applications

- Synchronous Rectification (SR) in DC–DC and AC–DC
- Primary Switch in Isolated DC–DC Converter
- Motor Drives
- Automotive 48 V System



DFNW5 (SO–8FL)
CASE 507BA

MARKING DIAGRAM



1D9N8W = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceabililty

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter		Symbol	Value	Unit
Drain–to–Source Voltage		V_{DSS}	80	V
Gate–to–Source Voltage		V_{GS}	±20	V
Continuous Drain Current (Note 1)	T_C = 25°C	I_D	201	A
	T_C = 100°C		142	
Power Dissipation (Note 1)	T_C = 25°C	P_D	164	W
Pulsed Drain Current	T_C = 25°C, t_p = 100 μs	I_{DM}	866	A
Pulsed Source Current (Body Diode)		I_{SM}	866	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	−55 to +175	°C
Source Current (Body Diode)		I_S	248	A
Single Pulse Avalanche Energy	I_{PK} = 58 A (Note 3)	E_{AS}	168	mJ
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)		T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The entire application environment impacts the thermal resistance values shown. They are not constants and are only valid for the particular conditions noted.
2. Actual continuous current will be limited by thermal and electromechanical application board design.
3. EAS of 168 mJ is based on started T_J = 25°C, I_{AS} = 58 A, V_{DD} = 64 V, V_{GS} = 10 V, 100% avalanche tested.

ORDERING INFORMATION

Device	Package	Shipping†
NVMFWS1D9N08XT1G	DFNW5 (Pb–Free)	1500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	0.91	°C/W
Thermal Resistance, Junction−to−Ambient (Notes 4, 5)	$R_{\theta JA}$	39	

4. Surface−mounted on FR4 board using 1 sq−in pad, 1 oz Cu.
5. $R_{\theta JA}$ is determined by the user's board design.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 1 mA		80			V
Drain−to−Source Breakdown Voltage (transient)	$\Delta V_{(BR)DSS}/\Delta T_J$	I_D = 1 mA, Referenced to 25C			31.6		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 80 V	T_J = 25°C			1	μA
			T_J = 125°C			250	
Gate−to−Source Leakage Current	I_{GSS}	V_{GS} = 20 V, V_{DS} = 0 V				100	nA
ON CHARACTERISTICS							
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 50 A			1.7	1.9	mΩ
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 252 μA		2.4		3.6	V
Negative Threshold Temperature Coefficient	$\Delta V_{GS(TH)}/\Delta T_J$	V_{GS} = V_{DS}, I_D = 252 μA,			−7.5		mV/°C
Forward Transconductance	g_{FS}	V_{DS} = 5 V, I_D = 50 A			158		S
CHARGES AND CAPACITANCES							
Input Capacitance	C_{ISS}	V_{DS} = 40 V, V_{GS} = 0 V, f = 1 MHz			4470		pF
Output Capacitance	C_{OSS}				1290		
Reverse Transfer Capacitance	C_{RSS}				20		
Output Charge	Q_{OSS}				93		
Total Gate Charge	$Q_{G(TOT)}$	V_{DD} = 40 V, I_D = 50 A, V_{GS} = 6 V			39		nC
		V_{DD} = 40 V, I_D = 50 A, V_{GS} = 10 V			63		
Threshold Gate Charge	$Q_{G(TH)}$				14		nC
Gate−to−Source Charge	Q_{GS}				21		
Gate−to−Drain Charge	Q_{GD}				10		
Gate Plateau Voltage	V_{GP}				4.7		V
Gate Resistance	R_G	f = 1 MHz			0.8		Ω
SWITCHING CHARACTERISTICS							
Turn−On Delay Time	$t_{d(ON)}$	Resistive Load, V_{GS} = 0/10 V, V_{DD} = 64 V, I_D = 50 A, R_G = 2.5 Ω			28		ns
Rise Time	t_r				12		
Turn−Off Delay Time	$t_{d(OFF)}$				43		
Fall Time	t_f				7		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	I_S = 50 A, V_{GS} = 0 V	T_J = 25°C		0.82	1.2	V
			T_J = 125°C		0.66		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, I_S = 50 A, dIS/dt = 1000 A/μs, V_{DD} = 64 V			26		ns
Charge Time	t_a				15		
Discharge Time	t_b				12		
Reverse Recovery Charge	Q_{RR}				211		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

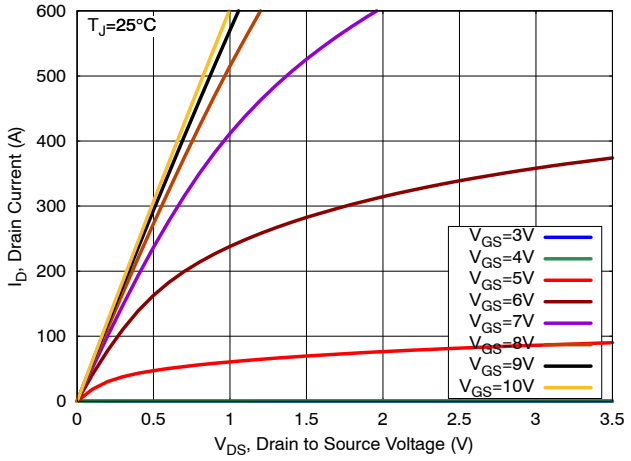


Figure 1. On−Region Characteristics

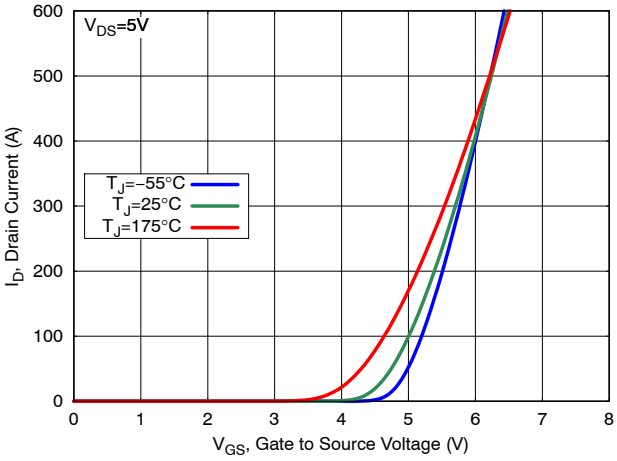


Figure 2. Transfer Characteristics

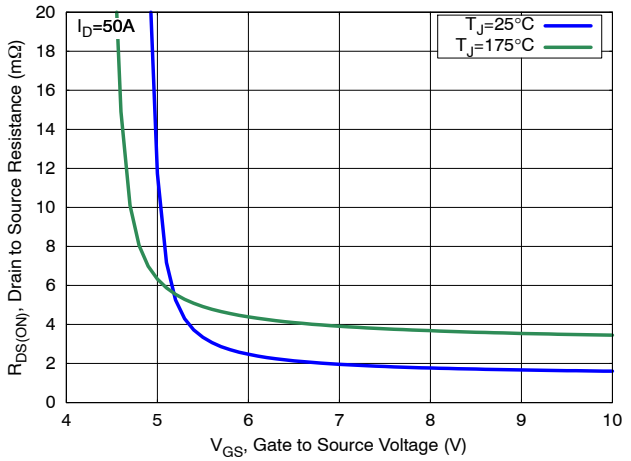


Figure 3. On−Resistance vs. Gate Voltage

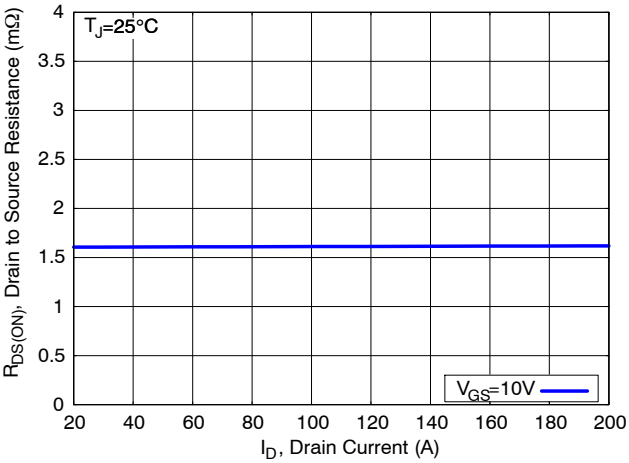


Figure 4. On−Resistance vs. Drain Current

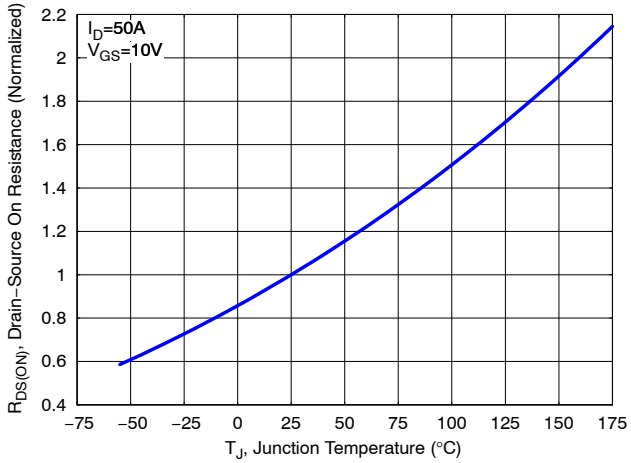


Figure 5. Normalized ON Resistance vs. Junction Temperature

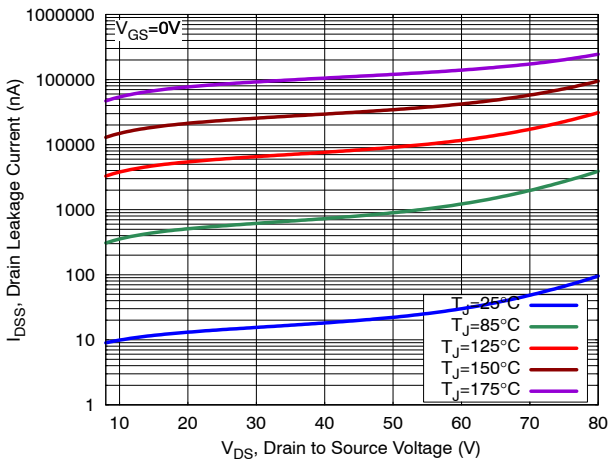


Figure 6. Drain Leakage Current vs Drain Voltage

TYPICAL CHARACTERISTICS

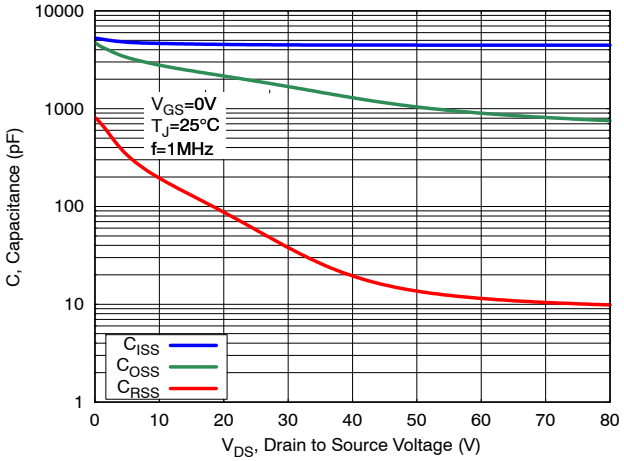


Figure 7. Capacitance Characteristics

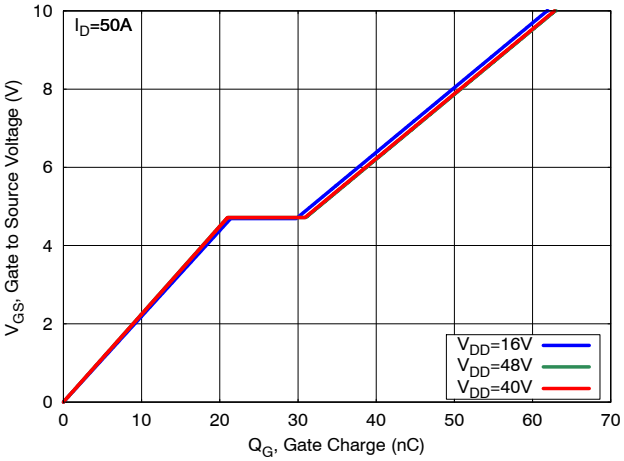


Figure 8. Gate Charge Characteristics

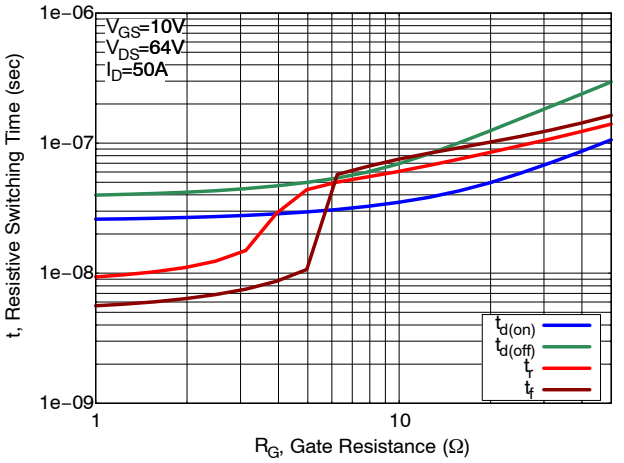


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

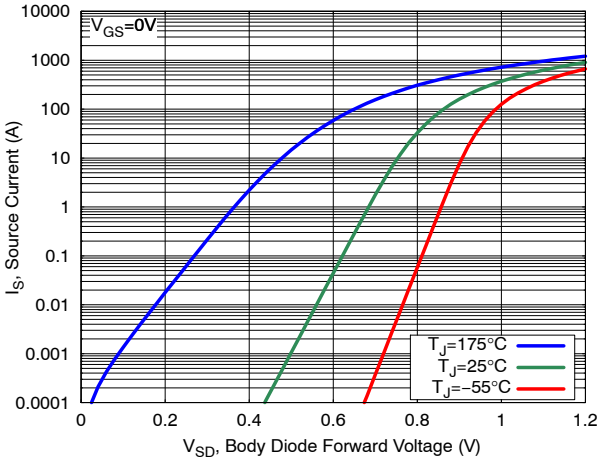


Figure 10. Diode Forward Characteristics

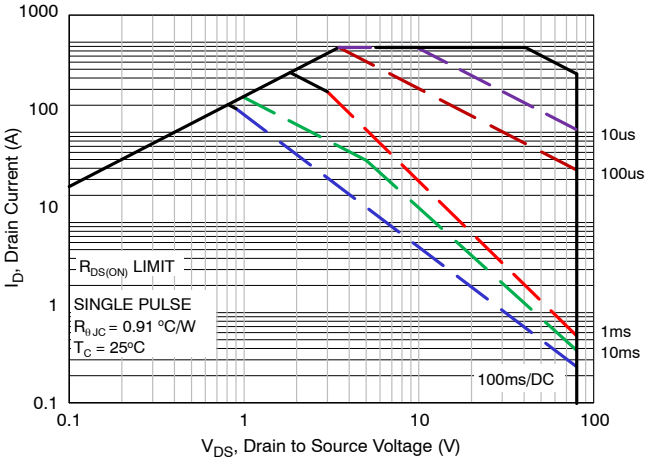


Figure 11. Safe Operating Area (SOA)

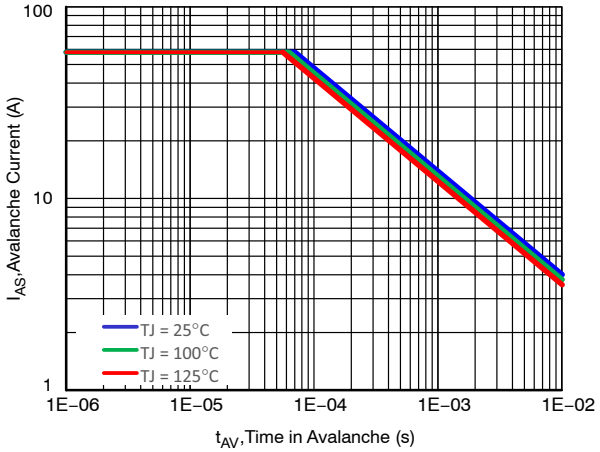


Figure 12. Avalanche Current vs Pulse Time (UIS)

TYPICAL CHARACTERISTICS

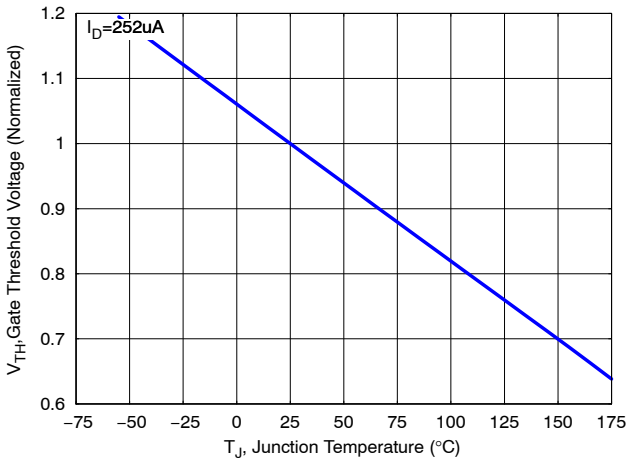


Figure 13. Gate Threshold Voltage vs Junction Temperature

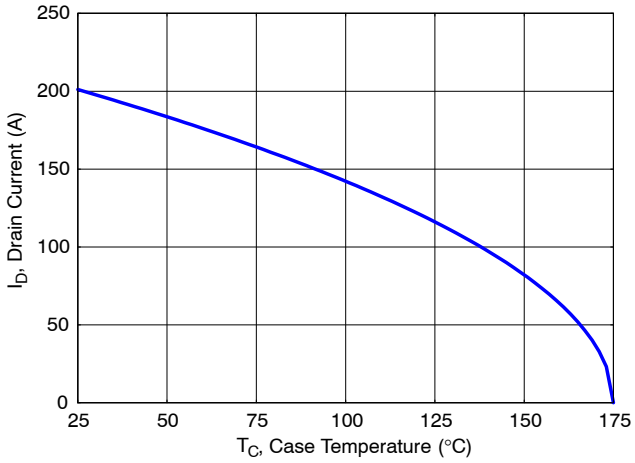


Figure 14. Maximum Current vs. Case Temperature

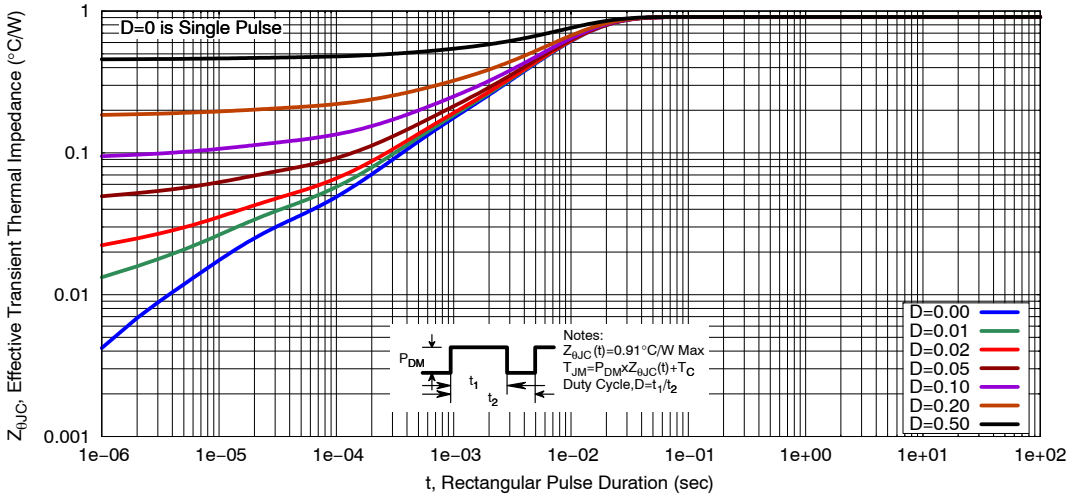
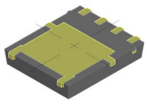
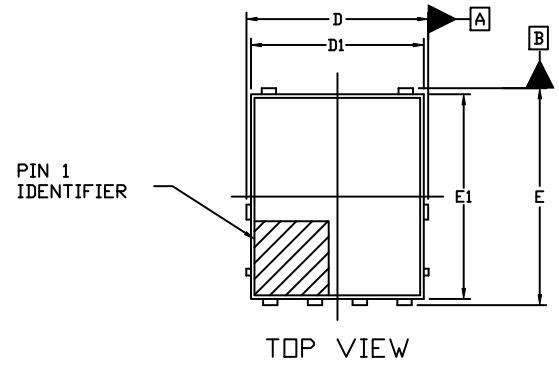


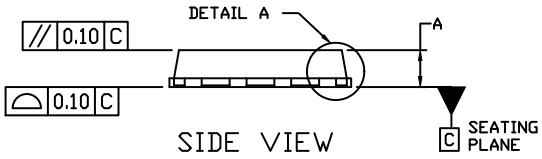
Figure 15. Transient Thermal Response

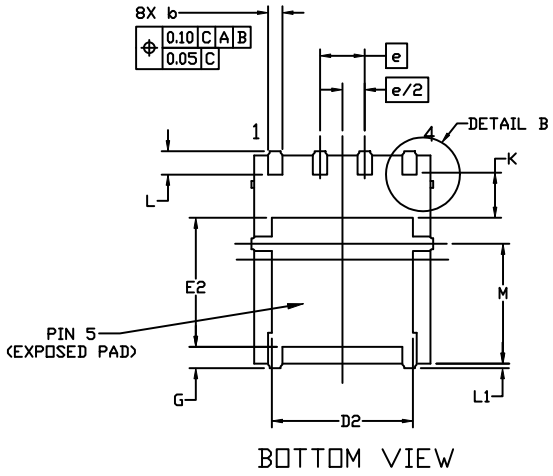


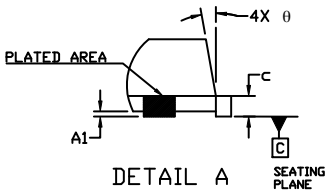
DFNW5 5x6 (FULL−CUT SO8FL WF)
CASE 507BA
ISSUE A

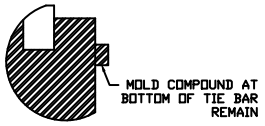
DATE 03 FEB 2021





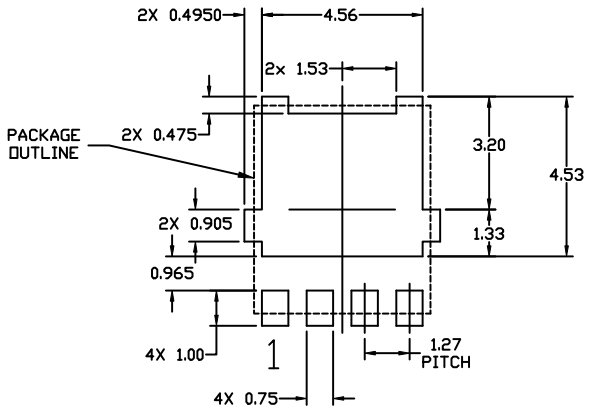






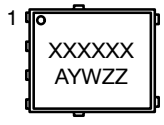
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
4. THIS PACKAGE CONTAINS WETTABLE FLANK DESIGN FEATURES TO AID IN FILLET FORMATION ON THE LEADS DURING MOUNTING.

	MILLIMETERS		
DIM	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.150 REF		
M	3.00	3.40	3.80
θ	0°	---	12°



* For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot " ▪", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	**DFNW5 5x6 (FULL−CUT SO8FL WF)**	**PAGE 1 OF 1**

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